TRADEMARK ASSIGNMENT COVER SHEET

Electronic Version v1.1
Stylesheet Version v1.2

ETAS ID: TM316235

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	SECURITY INTEREST

CONVEYING PARTY DATA

Name	Formerly	Execution Date	Entity Type
Soraa, Inc.		08/29/2014	CORPORATION: DELAWARE

RECEIVING PARTY DATA

Name:	Special Value Continuation Partners, LP
Street Address:	Two Embarcadero Center
Internal Address:	Suite 1670
City:	San Francisco
State/Country:	CALIFORNIA
Postal Code:	94111
Entity Type:	LIMITED PARTNERSHIP: DELAWARE
Name:	Tennenbaum Opportunities Partners V, LP
Street Address:	Two Embarcadero Center
Internal Address:	Suite 1670
City:	San Francisco
State/Country:	CALIFORNIA
Postal Code:	94111
Entity Type:	LIMITED PARTNERSHIP: DELAWARE
Name:	TCPC SBIC, LP
Street Address:	Two Embarcadero Center
Internal Address:	Suite 1670
City:	San Francisco
State/Country:	CALIFORNIA
Postal Code:	94111
Entity Type:	LIMITED PARTNERSHIP: DELAWARE

OP $190.00 86058247

PROPERTY NUMBERS Total: 7

Property Type	Number	Word Mark
Serial Number:	86058247	SORAA
Serial Number:	85895887	SORAA SNAP SYSTEM
Serial Number:	85495244	SIMPLY PERFECT
Registration Number:	4431751	SIMPLY PERFECT LIGHT
Registration Number:	4385048	SORAA

Property Type	Number	Word Mark
Registration Number:	4336144	SORAA GAN ON GAN
Registration Number:	4150651	SORAA

CORRESPONDENCE DATA

Fax Number: 9163629066

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

Phone: 916-362-9000
Email: mleonard@davisandleonard.com
Correspondent Name: Mark R. Leonard
Address Line 1: 8880 Cal Center Drive
Address Line 2: Suite 180
Address Line 4: Sacramento, CALIFORNIA 95826

NAME OF SUBMITTER:	Mark R. Leonard
SIGNATURE:	/Mark R. Leonard/
DATE SIGNED:	09/05/2014

Total Attachments: 39
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INTELLECTUAL PROPERTY SECURITY AGREEMENT

THIS INTELLECTUAL PROPERTY SECURITY AGREEMENT (as the same may be amended, restated, supplemented or otherwise modified from time to time, the "Agreement"), dated as of August 29, 2014, is made by each of the entities listed on the signature pages hereof (each a "Grantor" and, collectively, the "Grantors"), in favor of Obsidian Agency Services, Inc., a California corporation, as agent for Lenders (the "Agent").

W I T N E S S E T H:

WHEREAS, pursuant to the Loan and Security Agreement, dated as of August 29, 2014 (as the same may be amended, restated, supplemented or otherwise modified from time to time, the "Credit Agreement"), among Agent, Lenders and Soraa, Inc., ("Borrower"), Lenders have agreed to make Credit Extensions (collectively, "Loans") to Borrower upon the terms and subject to the conditions set forth therein; and

WHEREAS, pursuant to the Credit Agreement, Borrower is required to execute and deliver this Agreement.

NOW, THEREFORE, in consideration of the premises, to induce Lenders to enter into the Credit Agreement, to induce Lenders to make the Loans to Borrower thereunder, the mutual covenants herein contained, and for other good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, Grantors, jointly and severally, hereby agree with Agent as follows:

1. **Defined Terms**. Capitalized terms used herein without definition are used as defined in the Credit Agreement.

2. **Grant of Security Interest in Collateral**. Each Grantor, as collateral security for the prompt and complete payment and performance when due (whether at stated maturity, by acceleration or otherwise) of the Obligations, hereby mortgages, pledges and hypothecates to Agent, and grants to Agent a Lien on and security interest in, all of its right, title and interest in, to and under the following property of such Grantor (the "Collateral"):

(a) all Intellectual Property including, without limitation, those referred to on Schedule I hereto;

(b) all licenses providing for the grant by or to such Grantor of any right under any Intellectual Property, including, without limitation, those referred to on Schedule I hereto;

(c) all reissues, reexaminations, continuations, continuations-in-part, divisionals, renewals, reversions and extensions of the foregoing;

(d) all goodwill of the Grantor connected with the use of, and symbolized by, such Intellectual Property; and

(e) all income, royalties, proceeds and liabilities at any time due or payable or asserted under and with respect to any of the foregoing, including, without limitation, all rights to sue and recover at law or in equity for any past, present and future infringement, misappropriation, dilution, violation or other impairment thereof.

provided, that the foregoing is subject in all cases to the exclusions described in the Credit Agreement (including, without limitation, Exhibit A thereof), and shall not include any property of Borrower excluded from the definition "Collateral" under the Credit Agreement.

3. **Credit Agreement**. The security interest granted pursuant to this Agreement is granted in conjunction with the security interest granted to the Agent pursuant to the Credit Agreement and each Grantor hereby acknowledges and agrees that the rights and remedies of Agent and Lenders with respect to the security interest in the Collateral made and granted hereby are more fully set forth in the Credit Agreement, the terms and provisions of which are incorporated by reference herein as if fully set forth herein. In the event that any provision of this Agreement is deemed to conflict with the Credit Agreement, the provisions of the Credit Agreement shall control.

4. **Termination.** Upon the earlier of (i) the occurrence of the Collateral Release Condition and Borrower's providing Agent with evidence thereof that is reasonably satisfactory to Agent, and (ii) the payment in full of the Obligations, the security interest in the Intellectual Property granted under this Agreement shall automatically terminate, and Agent shall execute, acknowledge, and deliver to the Grantors an instrument in writing in recordable form releasing the security interest in the Intellectual Property under this Agreement.

5. **Grantor Remains Liable**. Each Grantor hereby agrees that, anything herein to the contrary notwithstanding, such Grantor shall assume full and complete responsibility for the prosecution, defense, enforcement or any other necessary or desirable actions in connection with their Intellectual Property subject to a security interest hereunder.

6. **Counterparts**. This Agreement may be executed in any number of counterparts and by different parties in separate counterparts, each of which when so executed shall be deemed to be an original and all of which taken together shall constitute one and the same agreement. Signature pages may be detached from multiple separate counterparts and attached to a single counterpart. Delivery of an executed signature page of this Agreement by facsimile transmission or electronic transmission shall be as effective as delivery of a manually executed counterpart hereof.

7. **Choice of Law, Venue, Jury Trial Waiver**.

(a) **Governing Law**. California law governs the Loan Documents without regard to principles of conflicts of law. Grantors and Agent each submit to the exclusive jurisdiction of the State and Federal courts in Los Angeles County, California; provided, however, that nothing in this Agreement shall be deemed to operate to preclude Agent from bringing suit or taking other legal action in any other jurisdiction to realize on the Collateral or any other security for the Obligations, or to enforce a judgment or other court order in favor of Agent. Grantors expressly submit and consent in advance to such jurisdiction in any action or suit commenced in any such court, and each Grantor hereby waives any objection that it may have based upon lack of personal jurisdiction, improper venue, or *forum non conveniens* and hereby consents to the granting of such legal or equitable relief as is deemed appropriate by such court. Each Grantor hereby waives personal service of the summons, complaints, and other process issued in such action or suit and agrees that service of such summons, complaints, and other process may be made by registered or certified mail addressed to Grantor at the address set forth in, or subsequently provided by Grantors in accordance with, Section 10 of the Credit Agreement and

that service so made shall be deemed completed upon the earlier to occur of Grantors' actual receipt thereof or three (3) days after deposit in the U.S. mails, proper postage prepaid.

(b) **Waiver of Jury Trial**. **TO THE FULLEST EXTENT PERMITTED BY APPLICABLE LAW, GRANTORS AND AGENT EACH WAIVE THEIR RIGHT TO A JURY TRIAL OF ANY CLAIM OR CAUSE OF ACTION ARISING OUT OF OR BASED UPON THE LOAN DOCUMENTS OR ANY CONTEMPLATED TRANSACTION, INCLUDING CONTRACT, TORT, BREACH OF DUTY AND ALL OTHER CLAIMS. THIS WAIVER IS A MATERIAL INDUCEMENT FOR BOTH PARTIES TO ENTER INTO THIS AGREEMENT. EACH PARTY HAS REVIEWED THIS WAIVER WITH ITS COUNSEL**.

(c) **Judicial Reference**. WITHOUT INTENDING IN ANY WAY TO LIMIT THE PARTIES' AGREEMENT TO WAIVE THEIR RESPECTIVE RIGHT TO A TRIAL BY JURY, if the above waiver of the right to a trial by jury is not enforceable, the parties hereto agree that any and all disputes or controversies of any nature between them arising at any time shall be decided by a reference to a private judge, mutually selected by the parties (or, if they cannot agree, by the Presiding Judge of Los Angeles County, California Superior Court) appointed in accordance with California Code of Civil Procedure Section 638 (or pursuant to comparable provisions of federal law if the dispute falls within the exclusive jurisdiction of the federal courts), sitting without a jury, in Los Angeles County, California; and the parties hereby submit to the jurisdiction of such court. The reference proceedings shall be conducted pursuant to and in accordance with the provisions of California Code of Civil Procedure §§ 638 through 645.1, inclusive. The private judge shall have the power, among others, to grant provisional relief, including without limitation, entering temporary restraining orders, issuing preliminary and permanent injunctions and appointing receivers. All such proceedings shall be closed to the public and confidential and all records relating thereto shall be permanently sealed. If during the course of any dispute, a party desires to seek provisional relief, but a judge has not been appointed at that point pursuant to the judicial reference procedures, then such party may apply to the Los Angeles County, California Superior Court for such relief. The proceeding before the private judge shall be conducted in the same manner as it would be before a court under the rules of evidence applicable to judicial proceedings. The parties shall be entitled to discovery which shall be conducted in the same manner as it would be before a court under the rules of discovery applicable to judicial proceedings. The private judge shall oversee discovery and may enforce all discovery rules and orders applicable to judicial proceedings in the same manner as a trial court judge.

(d) **Scope of Authority**. The parties agree that the selected or appointed private judge shall have the power to decide all issues in the action or proceeding, whether of fact or of law, and shall report a statement of decision thereon pursuant to California Code of Civil Procedure § 644(a). Nothing in this paragraph shall limit the right of any party at any time to exercise self-help remedies, foreclose against collateral, or obtain provisional remedies. The private judge shall also determine all issues relating to the applicability, interpretation, and enforceability of this paragraph.

[SIGNATURE PAGE FOLLOWS]

IN WITNESS WHEREOF, each Grantor has caused this Intellectual Property Security Agreement to be executed and delivered by its duly authorized officer as of the date first set forth above.

Soraa, Inc., as Grantor

By: _____
Name: Eric Williams
Title: Chief Financial Officer

Obsidian Agency Services, Inc., as Agent

_____
Name:
Title:

IN WITNESS WHEREOF, each Grantor has caused this Intellectual Property Security Agreement to be executed and delivered by its duly authorized officer as of the date first set forth above.

Soraa, Inc., as Grantor

By: _____
Name: Eric Williams
Title: Chief Financial Officer

Obsidian Agency Services, Inc., as Agent

_____
Name: HOWARD LEVKOWITZ
Title: PRESIDENT

SCHEDULE I
TO
INTELLECTUAL PROPERTY SECURITY AGREEMENT

See Attached

Intellectual Property

Patents:

Name of Patent	Patent Number	Date of Filing	Jurisdiction of Filing	Name of patent holder if other than Borrower
GALLIUM-NITRIDE-ON-HANDLE SUBSTRATE MATERIALS AND DEVICES AND METHOD OF MANUFACTURE	8,786,053	1/24/11	United States of America	
SURFACE MORPHOLOGY OF NON-POLAR GALLIUM NITRIDE CONTAINING SUBSTRATES	8,749,030	9/17/12	United States of America	
SYSTEM AND METHOD FOR PROVIDING COLOR LIGHT SOURCES IN PROXIMITY TO PREDETERMINED WAVELENGTH CONVERSION STRUCTURES	8,740,413	12/16/11	United States of America	
METHOD OF MAKING BULK INGAN SUBSTRATES AND DEVICES THEREON	8,729,559	10/13/11	United States of America	
POWER LIGHT EMITTING DIODE AND METHOD WITH CURRENT DENSITY OPERATION	8,686,458	6/28/13	United States of America	
GALLIUM AND NITROGEN CONTAINING TRILATERAL CONFIGURATION FOR OPTICAL DEVICES	8,686,431	10/25/11	United States of America	
SYSTEM AND METHOD FOR LED PACKAGING	8,674,395	5/29/12	United States of America	
ILLUMINATION SOURCE WITH REDUCED INNER CORE SIZE	8,643,257	2/11/11	United States of America	
ILLUMINATION SOURCE AND MANUFACTURING METHODS	8,618,742	2/11/11	United States of America	
POLARIZED WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND TRANSPARENT PHOSPHORS	8,618,560	9/20/12	United States of America	
METHOD AND SYSTEM FOR DICING SUBSTRATES CONTAINING GALLIUM AND NITROGEN MATERIAL	8,597,967	11/17/11	United States of	

			America	
METHOD AND SURFACE MORPHOLOGY OF NON-POLAR GALLIUM NITRIDE CONTAINING SUBSTRATES	8,575,728	7/13/12	United States of America	
OPTICAL DEVICES HAVING REFLECTION MODE WAVELENGTH MATERIAL	8,575,642	8/31/12	United States of America	
WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND PHOSPHORS	8,558,265	1/27/12	United States of America	
HIGH TEMPERATURE LED SYSTEM USING AN AC POWER SOURCE	8,541,951	11/17/11	United States of America	
ILLUMINATION SOURCE WITH DIRECT DIE PLACEMENT	8,525,396	2/11/11	United States of America	
METHOD AND SURFACE MORPHOLOGY OF NON-POLAR GALLIUM NITRIDE CONTAINING SUBSTRATES	8,524,578	7/13/12	United States of America	
POWER LIGHT EMITTING DIODE AND METHOD WITH CURRENT DENSITY OPERATION	8,502,465	9/20/10	United States of America	
LARGE AREA NONPOLAR OR SEMIPOLAR GALLIUM AND NITROGEN CONTAINING SUBSTRATE AND RESULTING DEVICES	8,492,185	7/13/12	United States of America	
METHOD FOR GROWTH OF INDIUM-CONTAINING NITRIDE FILMS	8,482,104	1/9/12	United States of America	
AMMONOTHERMAL METHOD FOR GROWTH OF BULK GALLIUM NITRIDE	8,465,588	7/1/11	United States of America	
POLYCRYSTALLINE GROUP III METAL NITRIDE WITH GETTER AND METHOD OF MAKING	8,461,071	12/9/09	United States of America	
PHOTONIC-CRYSTAL LIGHT EMITTING DIODE AND METHOD OF MANUFACTURE	8,455,894	9/29/09	United States of America	
PROCESS AND APPARATUS FOR LARGE-SCALE MANUFACTURING OF BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	8,444,765	9/6/11	United States of America	

HIGH PRESSURE APPARATUS WITH STACKABLE RINGS	8,435,347	9/27/10	United States of America	
APPARATUS AND METHOD FOR SEED CRYSTAL UTILIZATION IN LARGE-SCALE MANUFACTURING OF GALLIUM NITRIDE	8,430,958	8/3/09	United States of America	
TECHNIQUES OF FORMING OHMIC CONTACTS ON GAN LIGHT EMITTING DIODES	8,389,305	3/13/12	United States of America	
MICROCAVITY LIGHT EMITTING DIODE METHOD OF MANUFACTURE	8,354,679	9/29/09	United States of America	
NITRIDE CRYSTAL WITH REMOVABLE SURFACE LAYER AND METHODS OF MANUFACTURE	8,329,511	3/20/12	United States of America	
MODULAR LED LAMP AND MANUFACTURING METHODS	8,324,835	2/11/11	United States of America	
PROCESS AND APPARATUS FOR GROWING A CRYSTALLINE GALLIUM-CONTAINING NITRIDE USING AN AZIDE MINERALIZER	8,323,405	8/3/09	United States of America	
MULTI COLOR ACTIVE REGIONS FOR WHITE LIGHT EMITTING DIODE	8,314,429	9/13/10	United States of America	
SINGULATION METHOD AND RESULTING DEVICE OF THICK GALLIUM AND NITROGEN CONTAINING SUBSTRATES	8,313,964	6/17/11	United States of America	
HIGH INDIUM CONTAINING INGAN SUBSTRATES FOR LONG WAVELENGTH OPTICAL DEVICES	8,306,081	5/21/10	United States of America	
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH	8,303,710	6/4/09	United States of America	
POLARIZED WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND TRANSPARENT PHOSPHORS	8,299,473	4/6/10	United States of America	
GALLIUM AND NITROGEN CONTAINING TRIANGULAR OR DIAMOND-SHAPED CONFIGURATION FOR OPTICAL DEVICES	8,293,551	6/17/11	United States of America	
OPTICAL DEVICE WITH WAVELENGTH SELECTIVE REFLECTOR	8,269,245	10/28/10	United	

			States of America	
METHOD AND STRUCTURE FOR MANUFACTURE OF LIGHT EMITTING DIODE DEVICES USING BULK GAN	8,252,662	3/29/10	United States of America	
METHOD AND SURFACE MORPHOLOGY OF NON-POLAR GALLIUM NITRIDE CONTAINING SUBSTRATES	8,247,887	7/2/09	United States of America	
POLARIZATION DIRECTION OF OPTICAL DEVICES USING SELECTED SPATIAL CONFIGURATIONS	8,247,886	3/9/10	United States of America	
SYSTEM AND METHOD FOR LED PACKAGING	8,207,554	9/10/10	United States of America	
BACK-END PROCESSES FOR SUBSTRATES RE-USE	8,153,475	8/17/10	United States of America	
NITRIDE CRYSTAL WITH REMOVABLE SURFACE LAYER AND METHODS OF MANUFACTURE	8,148,801	8/24/09	United States of America	
TECHNIQUES OF FORMING OHMIC CONTACTS ON GAN LIGHT EMITTING DIODES	8,148,180	7/15/11	United States of America	
WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND PHOSPHORS	8,124,996	8/3/09	United States of America	
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH	8,097,081	6/5/08	United States of America	
LARGE-AREA BULK GALLIUM NITRIDE WAFER AND METHOD OF MANUFACTURE	8,048,225	9/9/09	United States of America	
PROCESS AND APPARATUS FOR LARGE-SCALE MANUFACTURING OF BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	8,021,481	8/4/09	United States of America	
LARGE-AREA SEED FOR AMMONOTHERMAL GROWTH OF BULK GALLIUM NITRIDE AND METHOD OF MANUFACTURE	7,976,630	9/9/09	United States of America	
HEATSINK	D694,722	6/4/12	United States of	

			America	
HEATSINK FOR LED	D662,900	8/15/11	United States of America	
HEATSINK	D662,899	8/15/11	United States of America	
POWER LIGHT EMITTING DIODE AND METHOD WITH CURRENT DENSITY OPERATION	10-1368906	9/20/10	Republic of Korea	
REFLECTION MODE PACKAGE FOR OPTICAL DEVICES USING GALLIUM AND NITROGEN CONTAINING MATERIALS	5567149	2/3/11	Japan	
IMPROVED ACCESSORIES FOR LED LAMPS	5540229	8/31/12	Japan	
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH	5536046	6/4/09	Japan	
POLYCRYSTALLINE GROUP III METAL NITRIDE WITH GETTER AND METHOD OF MAKING	5476637	12/11/09	Japan	
WHITE LIGHT APPARATUS AND METHOD	202011110024.7	2/3/11	Germany	
IMPROVED ACCESSORIES FOR LED LAMPS	ZL 201220446378.0	9/3/12	China	

Patent Applications (Note: Applications marked by "*" indicate that the application has been confidentially filed with the USPTP):

Name of Patent Application	Patent Application Number	Date of Filing	Jurisdiction of Filing	Name of application holder if other than Borrower
CAPSULE FOR HIGH PRESSURE PROCESSING AND METHOD OF USE FOR SUPERCRITICAL FLUIDS*	12/133,365	6/5/08	United States of America	
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH*	12/334,418	12/12/08	United States of America	
SELECTIVE AREA EPITAXY GROWTH METHOD AND STRUCTURE*	12/482,440	6/10/09	United States of America	
HEATER DEVICE AND METHOD FOR HIGH PRESSURE PROCESSING OF CRYSTALLINE MATERIALS*	12/484,095	6/12/09	United States of America	

SOLID-STATE OPTICAL DEVICE HAVING ENHANCED INDIUM CONTENT IN ACTIVE REGIONS*	12/484,924	6/15/09	United States of America	
COPACKING CONFIGURATIONS FOR NONPOLAR GAN AND/OR SEMIPOLAR GAN LEDS*	12/491,176	6/24/09	United States of America	
HIGH QUALITY LARGE AREA BULK NON-POLAR OR SEMIPOLAR GALLIUM BASED SUBSTRATES AND METHODS*	12/497,969	7/6/09	United States of America	
PROCESS FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF GALLIUM NITRIDE BOULES*	12/534,844	8/3/09	United States of America	
TEXTURED-SURFACE LIGHT EMITTING DIODE AND METHOD OF MANUFACTURE*	12/569,841	9/29/09	United States of America	
METHOD AND SYSTEM FOR THIN FILM PROCESSING USING SHOWER HEAD DEVICE*	12/573,820	10/5/09	United States of America	
SCALABLE, COMPACT, RAPID HYDROTHERMAL METHOD FOR CRYSTAL GROWTH*	12/636,683	12/11/09	United States of America	
PLANT AND METHOD FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF GALLIUM NITRIDE BOULES*	12/697,171	1/29/10	United States of America	
STRAIN MITIGATION USING SELECTIVE AREA EPITAXY GROWTH METHOD AND STRUCTURE*	12/727,148	3/18/10	United States of America	
GAN CONTAINING OPTICAL DEVICES AND METHOD WITH ESD STABILITY*	12/785,953	5/24/10	United States of America	
LIGHT EMITTING DIODE DEVICE WITH A PLURALITY OF ROUGHENED SURFACES, AND METHOD FOR FABRICATING THEREOF*	12/861,765	8/23/10	United States of America	
BLUE GREEN ACTIVE REGION AND RED PHOSPHOR WHITE LEDS*	12/880,889	9/13/10	United States of America	
REFLECTION MODE WAVELENGTH CONVERSION MATERIAL FOR OPTICAL DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS*	12/887,207	9/21/10	United States of America	

METHOD FOR SYNTHESIS OF HIGH QUALITY LARGE AREA BULK GALLIUM BASED CRYSTALS*	12/988,772	10/11/10	United States of America	
HIGHLY POLARIZED WHITE LIGHT SOURCE BY COMBINING BLUE LED ON SEMIPOLAR OR NONPOLAR GAN WITH YELLOW LED ON SEMIPOLAR OR NONPOLAR GAN*	12/995,946	12/2/10	United States of America	
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH*	13/013,697	1/25/11	United States of America	
QUANTUM DOT WAVELENGTH CONVERSION FOR OPTICAL DEVICES USING NONPOLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS*	13/014,622	1/26/11	United States of America	
REFLECTION MODE PACKAGE FOR OPTICAL DEVICES USING GALLIUM AND NITROGEN CONTAINING MATERIALS*	13/019,521	2/2/11	United States of America	
WHITE LIGHT APPARATUS AND METHOD*	13/019,897	2/2/11	United States of America	
SEMI-INSULATING GROUP III METAL NITRIDE AND METHOD OF MANUFACTURE*	13/041,199	3/4/11	United States of America	
QUANTUM DOT WAVELENGTH CONVERSION FOR HERMETICALLY SEALED OPTICAL DEVICES*	13/135,087	6/23/11	United States of America	
LARGE AREA NITRIDE CRYSTAL AND METHOD FOR MAKING IT*	13/160,307	6/14/11	United States of America	
SEALED LED PACKAGE*	13/210,769	8/16/11	United States of America	
SYSTEM AND METHOD FOR SELECTED PUMP LEDs WITH MULTIPLE PHOSPHORS*	13/211,145	8/16/11	United States of America	
HIGH INTENSITY LIGHT SOURCE*	13/269,193	10/7/11	United States of America	
ILLUMINATION SOURCES WITH THERMALLY-ISOLATED ELECTRONICS*	13/274,489	10/17/11	United States of America	

METHOD FOR MANUFACTURE OF BRIGHT GAN LEDS USING A SELECTIVE REMOVAL PROCESS*	13/304,182	11/23/11	United States of America	
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH*	13/343,563	1/4/12	United States of America	
LED LIGHT SYSTEM WITH SELECTIVE REFLECTOR MEMBER*	13/357,315	1/24/12	United States of America	
GALLIUM AND NITROGEN CONTAINING TRIANGULAR OR DIAMOND-SHAPED CONFIGURATION FOR OPTICAL DEVICES*	13/357,578	1/24/12	United States of America	
METHOD AND RESULTING DEVICE FOR PROCESSING PHOSPHOR MATERIALS IN LIGHT EMITTING DIODE APPLICATIONS*	13/359,846	1/27/12	United States of America	
METHOD AND SYSTEM FOR EPITAXY PROCESSES ON MISCUT BULK SUBSTRATES*	13/431,834	3/27/12	United States of America	
METHOD AND RESULTING DEVICE FOR PROCESSING PHOSPHOR MATERIALS IN LIGHT EMITTING DIODE APPLICATIONS*	13/465,976	5/7/12	United States of America	
PROCESS FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF GALLIUM NITRIDE BOULES*	13/472,356	5/15/12	United States of America	
HIGH INTENSITY LIGHT SOURCE WITH INTERCHANGEABLE OPTICS*	13/480,767	5/25/12	United States of America	
METHOD AND SYSTEM FOR DICING SUBSTRATES CONTAINING GALLIUM AND NITROGEN MATERIAL WITH CONDUCTIVE CORE VIA STRUCTURES*	13/491,483	6/7/12	United States of America	
FILAMENT-LIKE LIGHT SOURCE FOR LED LAMPS*	13/535,142	6/27/12	United States of America	
METHODS AND APPARATUS FOR SOLVOTHERMAL CRYSTAL GROWTH AND METHOD OF USE*	13/538,426	6/29/12	United States of America	
POLARIZATION DIRECTION OF OPTICAL DEVICES USING SELECTED SPATIAL CONFIGURATIONS*	13/553,691	7/19/12	United States of America	

HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH*	13/556,105	7/23/12	United States of America	
METHOD AND SYSTEM FOR FABRICATING OPTICAL DEVICES*	13/593,128	8/23/12	United States of America	
LARGE AREA, LOW-DEFECT GALLIUM-CONTAINING NITRIDE CRYSTALS, METHOD OF MAKING, AND METHOD OF USE*	13/600,191	8/30/12	United States of America	
BLUE LIGHT EMITTING DIODES GROWN ON (30-3-2) ORIENTED BULK GAN SUBSTRATES*	13/629,366	9/27/12	United States of America	
APPARATUS FOR LARGE VOLUME AMMONOTHERMAL MANUFACTURE OF GALLIUM NITRIDE CRYSTALS AND METHODS OF USE*	13/656,615	10/19/12	United States of America	
APPARATUS FOR LARGE VOLUME AMMONOTHERMAL MANUFACTURE OF GALLIUM NITRIDE CRYSTALS AND METHODS OF USE*	13/657,551	10/22/12	United States of America	
CONTACTS FOR AN N-TYPE GALLIUM AND NITROGEN SUBSTRATE FOR OPTICAL DEVICES*	13/723,968	12/21/12	United States of America	
LARGE AREA NITRIDE CRYSTAL AND METHOD FOR MAKING IT*	13/731,453	12/31/12	United States of America	
METHODS AND DEVICES FOR LIGHT EXTRACTION FROM A GROUP III-NITRIDE VOLUMETRIC LED USING SURFACE AND SIDEWALL ROUGHENING*	13/781,633	2/28/13	United States of America	
LIGHT EMITTING DIODES WITH LOW REFRACTIVE INDEX MATERIAL LAYERS TO REDUCE LIGHT GUIDING EFFECTS*	13/787,582	3/6/13	United States of America	
ILLUMINATION SOURCE WITH DIRECT DRIVER PLACEMENT*	13/855,423	4/2/13	United States of America	
PROVIDING REMOTE BLUE PHOSPHORS IN AN LED LAMP*	13/856,613	4/4/13	United States of America	
COMPACT LENS FOR HIGH INTENSITY LIGHT SOURCE*	13/865,760	4/18/13	United States of America	

SAFETY OF USER-INSTALLED LED LAMPS*	13/868,881	4/23/13	United States of America	
LED LAMPS WITH IMPROVED QUALITY OF LIGHT*	13/886,547	5/3/13	United States of America	
COMPACT LENS FOR HIGH INTENSITY LIGHT SOURCE*	13/894,203	5/14/13	United States of America	
POLYCRYSTALLINE GROUP III METAL NITRIDE WITH GETTER AND METHOD OF MAKING*	13/894,220	5/14/13	United States of America	
LENS OVERMOLDING ATOP AN OPTICAL DEVICE FOR IMPROVED SUBSTRATE UTILIZATION*	13/904,237	5/29/13	United States of America	
PROCESS FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF SEMIPOLAR GALLIUM NITRIDE BOULES*	13/908,836	6/3/13	United States of America	
ACCESSORIES FOR LED LAMPS*	13/909,752	6/4/13	United States of America	
LED LAMPS AND CONTROLLERS FOR LIGHTING FIXTURES*	13/915,432	6/11/13	United States of America	
CONTACTS FOR AN N-TYPE GALLIUM AND NITROGEN SUBSTRATE FOR OPTICAL DEVICES*	13/937,338	7/9/13	United States of America	
ILLUMINATION SOURCE WITH REDUCED WEIGHT*	13/945,763	7/18/13	United States of America	
THICK-FILM LIGHT EMITTING DIODES ON BULK GALLIUM NITRIDE OR GALLIUM NITRIDE TEMPLATE*	13/947,970	7/22/13	United States of America	
ILLUMINATION SOURCE WITH DIRECT DIE PLACEMENT*	13/959,422	8/5/13	United States of America	
HIGH TEMPERATURE LED SYSTEM USING AN AC POWER SOURCE*	13/973,213	8/22/13	United States of America	

METHOD FOR QUANTIFICATION OF EXTENDED DEFECTS IN GALLIUM-CONTAINING NITRIDE CRYSTALS*	14/013,753	8/29/13	United States of America	
ACCESSORIES FOR LED LAMPS*	14/014,112	8/29/13	United States of America	
INDEX-MATCHED COMPOSITION FOR PHOSPHOR-CONTAINING LAYERS HAVING IMPROVED THERMAL CONDUCTIVITY AND METHOD OF MAKING*	14/022,587	9/10/13	United States of America	
ULTRAPURE MINERALIZERS AND METHODS FOR NITRIDE CRYSTAL GROWTH*	14/033,107	9/20/13	United States of America	
WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND PHOSPHORS*	14/035,693	9/24/13	United States of America	
POWER LIGHT EMITTING DIODE AND METHOD WITH UNIFORM CURRENT DENSITY OPERATION*	14/040,379	9/27/13	United States of America	
INDIUM GALLIUM NITRIDE LIGHT EMITTING DEVICES*	14/054,234	10/15/13	United States of America	
LOW-COST LED WITH HIGH COLOR POINT UNIFORMITY*	14/054,597	10/15/13	United States of America	
HIGH-TEMPERATURE ULTRA-LOW RIPPLE MULTI-STAGE LED DRIVER AND LED CONTROL CIRCUITS*	14/075,936	11/8/13	United States of America	
POLARIZED WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND TRANSPARENT PHOSPHORS*	14/086,792	11/21/13	United States of America	
HIGH QUALITY GROUP-III METAL NITRIDE CRYSTALS, MEHODS OF MAKING, AND METHODS OF USE*	14/089,281	11/25/13	United States of America	
ILLUMINATION SOURCE WITH DIRECT DIE PLACEMENT*	14/097,043	12/4/13	United States of America	
SYSTEM AND METHOD FOR PROVIDING LIGHT SOURCES IN PROXIMITY TO THERMALLY CONDUCTIVE OMNIDIRECTIONAL REFLECTORS*	14/097,481	12/5/13	United States of America	

LED LAMPS AND CONTROLLERS FOR LIGHTING FIXTURES*	14/098,244	12/5/13	United States of America	
DENSE-LUMINESCENT-MATERIALS-COATED VIOLET LEDS*	14/135,098	12/19/13	United States of America	
ACCESSORIES FOR LED LAMP SYSTEMS*	14/166,692	1/28/14	United States of America	
HIGHLY POLARIZED WHITE LIGHT SOURCE BY COMBINING BLUE LED ON SEMIPOLAR OR NONPOLAR GAN WITH YELLOW LED ON SEMIPOLAR OR NONPOLAR GAN*	14/171,321	2/3/14	United States of America	
SYSTEM AND METHOD FOR LED PACKAGING*	14/171,885	2/4/14	United States of America	
GALLIUM AND NITROGEN CONTAINING TRILATERAL CONFIGURATION FOR OPTICAL DEVICES*	14/181,386	2/14/14	United States of America	
APPORTIONING OPTICAL PROJECTION PATHS IN AN LED LAMP*	14/191,679	2/27/14	United States of America	
POLARIZED WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND TRANSPARENT PHOSPHORS*	14/191,950	2/27/14	United States of America	
MULTI-PART HEAT EXCHANGER FOR LED LAMPS*	14/199,398	3/6/14	United States of America	
LED LAMPS WITH IMPROVED AC-DC DRIVER CHARACTERISTICS*	14/211,606	3/14/14	United States of America	
DOUBLE HETEROSTRUCTURE LED FOR GALLIUM AND NITROGEN CONTAINING DEVICES*	14/212,547	3/14/14	United States of America	
POWER LIGHT EMITTING DIODE FOR LIGHTING*	14/231,414	3/31/14	United States of America	
LARGE AREA SEED CRYSTAL FOR AMMONOTHERMAL CRYSTAL GROWTH AND METHOD OF MAKING*	14/249,708	4/10/14	United States of America	

SYSTEM AND METHOD FOR PROVIDING COLOR LIGHT SOURCES IN PROXIMITY TO PREDETERMINED WAVELENGTH CONVERSION STRUCTURES*	14/256,670	4/18/14	United States of America	
LIGHT EMITTING DIODES HAVING DIELECTRIC SEALS AND METHODS OF FORMING DIELECTRIC SEALS*	14/294,251	6/3/14	United States of America	
GALLIUM-NITRIDE-ON-HANDLE SUBSTRATE MATERIALS AND DEVICES AND METHOD OF MANUFACTURE*	14/301,520	6/11/14	United States of America	
SURFACE MORPHOLOGY OF NON-POLAR GALLIUM NITRIDE CONTAINING SUBSTRATES*	14/302,250	6/11/14	United States of America	
LED LAMPS WITH IMPROVED QUALITY OF LIGHT*	14/310,957	6/20/14	United States of America	
CIRCADIAN-FRIENDLY LED LIGHT SOURCE*	14/316,685	6/26/14	United States of America	
HIGH INTENSITY LIGHT SOURCE*	14/320,076	6/30/14	United States of America	
GLARE REDUCED COMPACT LENS FOR HIGH INTENSITY LIGHT SOURCE*	14/336,276	7/21/14	United States of America	
TRIANGULAR SEMICONDUCTOR DIE*	29/439,581	12/12/12	United States of America	
HEAT SINK*	29/441,108	12/31/12	United States of America	
ARRAY OF TRIANGULAR SEMICONDUCTOR DICE*	29/441,116	12/31/12	United States of America	
DIAMOND-SHAPED SEMICONDUCTOR DIE*	29/441,960	1/11/13	United States of America	
LED LAMP AND ACCESSORY*	29/454,826	5/14/13	United States of America	

ARRAY OF TRIANGULAR SEMICONDUCTOR DICE*	29/456,725	6/3/13	United States of America	
TRIANGULAR SEMICONDUCTOR DIE*	29/456,727	6/3/13	United States of America	
LED LAMP WITH ACCESSORY*	29/458,298	6/18/13	United States of America	
HEATSINK*	29/469,709	10/14/13	United States of America	
LED LAMP*	29/475,763	12/6/13	United States of America	
LED LAMP*	29/475,764	12/6/13	United States of America	
LED LAMP*	29/475,766	12/6/13	United States of America	
LED LAMP*	29/475,769	12/6/13	United States of America	
SPOT LAMP*	29/489,662	5/1/14	United States of America	
FLOOD LAMP*	29/490,770	5/13/14	United States of America	
LED LAMP*	29/492,704	6/2/14	United States of America	
LED LIGHT MODULE*	29/492,740	6/2/14	United States of America	
SPOT LAMP*	29/495,601	7/2/14	United States of America	

FLOOD LAMP*	29/495,625	7/2/14	United States of America	
CIRCADIAN-FRIENDLY LED LIGHT SOURCE*	61/871,525	8/29/13	United States of America	
TRANSPARENT GROUP Ill METAL NITRIDE AND METHOD OF MANUFACTURE*	61/877,875	9/13/13	United States of America	
SMALL LED SOURCE WITH HIGH BRIGHTNESS AND HIGH EFFICIENCY*	61/899,723	11/4/13	United States of America	
COMPUTER-AIDED LED LAMP DESIGN METHOD AND MANUFACTURE OF SAME USING LAMP PROPERTIES AND CONSTRAINTS*	61/912,348	12/5/13	United States of America	
INTERCHANGEABLE LED LAMP ACCESSORY KIT*	61/930,784	1/23/14	United States of America	
HIGH-PERFORMANCE LED FABRICATION*	61/936,000	2/5/14	United States of America	
CONTROLLING OXYGEN CONCENTRATION LEVELS DURING PROCESSING OF HIGHLY-REFLECTIVE CONTACTS*	61/989,693	5/7/14	United States of America	
HIGH EFFICIENCY LED POWER CONVERTER*	62/016,899	6/25/14	United States of America	
GIMBAL FOR SNAP*	62/026,305	7/18/14	United States of America	
REUSABLE NITRIDE WAFER, METHOD OF MAKING, AND METHOD OF USE*	62/026,777	7/21/14	United States of America	
SORAA	86/058,247	9/6/13	United States of America	
DENSE-LUMINESCENT-MATERIALS-COATED VIOLET LEDS	10-2013-0161329	12/23/13	Republic of Korea	

SYSTEM AND METHOD FOR SELECTED PUMP LEDS WITH MULTIPLE PHOSPHORS	10-2013-7006992	8/19/11	Republic of Korea	
TRIANGULAR SEMICONDUCTOR DIE	30-2013-0030432	6/12/13	Republic of Korea	
TRIANGULAR SEMICONDUCTOR DIE	30-2013-0030434	6/12/13	Republic of Korea	
ARRAY OF TRIANGULAR SEMICONDUCTOR DICE	30-2013-0033360	6/28/13	Republic of Korea	
ARRAY OF TRIANGULAR SEMICONDUCTOR DICE	30-2013-0033361	6/28/13	Republic of Korea	
PROCESS FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF GALLIUM NITRIDE BOULES	P.394857	8/4/09	Poland	
POLYCRYSTALLINE GROUP III METAL NITRIDE WITH GETTER AND METHOD OF MAKING	P-396376	12/11/09	Poland	
LIGHT EMITTING DIODES WITH LOW REFRACTIVE INDEX MATERIAL LAYERS TO REDUCE LIGHT GUIDING EFFECTS	PCT/US2013/029453	3/6/13	PCT	
LARGE AREA NITRIDE CRYSTAL AND METHOD FOR MAKING IT	2011-134782	6/17/11	Japan	
PLANT AND METHOD FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF GALLIUM NITRIDE BOULES	2011-17315	1/29/11	Japan	
WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND PHOSPHORS	2011-522148	8/3/09	Japan	
PROCESS FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF GALLIUM NITRIDE BOULES	2011-522191	8/4/09	Japan	
IMPROVED SEMI-INSULATING GROUP III METAL NITRIDE AND METHOD OF MANUFACTURE	2011-53647	3/11/11	Japan	
HEATSINK FOR LED	2012-002987	2/14/12	Japan	
METHODS AND SYSTEMS FOR EPTAXIAL PROCESSES ON MUSCUT BULK SUBSTRATES	2012-079345	3/30/12	Japan	
ILLUMINATION SOURCE WITH REDUCED INNER CORE SIZE	2012-26856	2/10/12	Japan	
HEATSINK	2012-29611	12/4/12	Japan	
RAPID GROWTH METHOD AND STRUCTURES FOR GALLIUM AND NITROGEN CONTAINING ULTRA-THIN EPITAXIAL STRUCTURES FOR DEVICES	2012-525744	8/20/10	Japan	
POWER LIGHT EMITTING DIODE AND METHOD WITH CURRENT DENSITY OPERATION	2012-529969	9/20/10	Japan	

WHITE LIGHT APPARATUS AND METHOD	2012-552086	2/3/11	Japan	
LED LAMPS WITH IMPROVED QUALITY OG LIGHT	2013-097298	5/7/13	Japan	
HEATSINK	2013-10320	12/4/12	Japan	
PROCESS FOR LARGE-SCALE AMMONO THERMAL MANUFACTURING OF SEMIPOLAR GALLIUM NITRIDE BOULES	2013-117510	6/4/13	Japan	
INDIUM GALLIUM NITRIDE LIGHT EMITTING DEVICES	2013-215853	10/16/13	Japan	
DENSE-LUMINESCENT-MATERIALS -COATED VIOLET LEDS	2013-263760	12/20/13	Japan	
GALLIUM AND NITROGEN CONTAINING TRIANGULAR OR DIAMOND-SHAPED CONFIGURATION FOR OPTICAL DEVICES	2013-515583	6/20/11	Japan	
SYSTEM AND METHOD FOR SELECTED PUMP LEDS WITH MULTIPLE PHOSHORS	2013-525007	8/19/11	Japan	
HIGH INTENSITY LIGHT SOURCE	2013-532992	10/7/11	Japan	
POLYCRYSTALLINE GROUP III METAL NITRIDE WITH GETTER AND METHOD OF MAKING	2014-010998	12/11/09	Japan	
LED LAMP	2014-012190	6/5/14	Japan	
LED LAMP	2014-012191	6/5/14	Japan	
LED LAMP	2014-012192	6/5/14	Japan	
LED LAMP	2014-012193	6/5/14	Japan	
IMPROVED ACCESSORIES FOR LED LAMPS	2014-070142	8/31/12	Japan	
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH	2014-088867	6/4/09	Japan	
ARRAY OF TRIANGULAR SEMICONDUCTOR DICE	D2013-014511	6/27/13	Japan	
TRIANGULAR SEMICONDUCTOR DIE	D2013-13276	6/12/13	Japan	
ARRAY OF TRIANGULAR SEMICONDUCTOR DICE	D2013-17841	6/27/13	Japan	

TRIANGULAR SEMICONDUCTOR DIE	D2013-18085	6/12/13	Japan	
TRIANGULAR SEMICONDUCTOR DIE	D2013-18090	6/12/13	Japan	
LED LAMP AND ACCESSORY	JP2013-026697	11/14/13	Japan	
HIGH QUALITY GROUP-III METAL NITRIDE CRYSTALS,METHODS OF MAKING, AND METHODS OF USE	JP2013-243510	11/26/13	Japan	
LED LAMP	40201400488.9	6/6/14	Germany	
ILLUMINATION SOURCE WITH REDUCED INNER CORE SIZE	102012002859.8	2/13/12	Germany	
METHODS AND SYSTEMS FOR EPITAXIAL PROCESSES ON MISCUT BULK SUBSTRATES	102012006613.9	3/30/12	Germany	
IMPROVED ACCESSORIES FOR LED LAMPS	102012017255.9	8/31/12	Germany	
DENSE-LUMINESCENT-MATERIALS -COATED VIOLET LEDS	102013114723.2	12/20/13	Germany	
POWER LIGHT EMITING DIODE AND METHOD WITH CURENT DENSITY OPERATION	112010003700.0	9/20/10	Germany	
WHITE LIGHT APPARATUS AND METHOD	112011100183.5	2/3/11	Germany	
REFLECTION MODE PACKAGE FOR OPTICAL DEVICES USING GALLIUM AND NITROGEN CONTAINING MATERIALS	112011100435.4	2/3/11	Germany	
GALLIUM AND NITROGEN CONTAINING TRIANGULAR OR DIAMOND-SHAPED CONFIGURATION FOR OPTICAL DEVICES	112011102068.6	6/20/11	Germany	
LED LAMP AND ACCESSORY	402013101118.1	11/14/13	Germany	
LED LAMP	402014100488.9	6/6/14	Germany	
LED LAMP	402014100488.9	6/6/14	Germany	
LED LAMP	402014100488.9	6/6/14	Germany	
RAPID GROWTH METHOD AND STRUCTURES FOR GALLIUM AND NITROGEN CONTAINING ULTRA-THIN EPITAXIAL STRUCTURES FOR DEVICES	11 2010 003 358.7	8/20/10	Germany	
SYSTEM AND METHOD FOR SELECTED PUMP LEDS WITH MULTIPLE PHOSPHORS	11 2011 102 386.3	8/19/11	Germany	

TRIANGULAR SEMICONDUCTOR DIE	40 2013 002 758.0	6/12/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE	40 2013 002 758.0	6/12/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE	40 2013 002 758.0	6/12/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE	40 2013 002 758.0	6/12/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE	40 2013 002 758.0	6/12/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE	40 2013 002 758.0	6/12/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE	40 2013 002 758.0	6/12/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE	40 2013 002 758.0	6/12/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE	40 2013 002 758.0	6/12/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE	40 2013 002 758.0	6/12/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE II	40 2013 002 981.8	6/27/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE II	40 2013 002 981.8	6/27/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE II	40 2013 002 981.8	6/27/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE II	40 2013 002 981.8	6/27/13	Germany	
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TRIANGULAR SEMICONDUCTOR DIE II	40 2013 002 981.8	6/27/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE II	40 2013 002 981.8	6/27/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE II	40 2013 002 981.8	6/27/13	Germany	

TRIANGULAR SEMICONDUCTOR DIE II	40 2013 002 981.8	6/27/13	Germany	
TRIANGULAR SEMICONDUCTOR DIE II	40 2013 002 981.8	6/27/13	Germany	
LED LAMPS WITH IMPROVED QUALITY OF LIGHT	DE 10 2013 007 698.6	5/3/13	Germany	
HIGH INTENSITY LIGHT SOURCE	DE112011102961.6	10/7/11	Germany	
HEATSINK FOR LED	1314926	2/14/12	European Union	
HEAT SINK	002146449	12/3/12	European Union	
HEAT SINK	002146449	12/3/12	European Union	
WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND PHOSPHORS	09805406.7	8/3/09	European Patent Office	
WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND PHOSPHORS	200980134723.8	8/3/09	China	
PROCESS FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF GALLIUM NITRIDE BOULES	200980134876.2	8/4/09	China	
POLYCRYSTALLINE GROUP III METAL NITRIDE WITH GETTER AND METHOD OF MAKING	200980154756.9	12/11/09	China	
RAPID GROWTH METHOD AND STRUCTURES FOR GALLIUM AND NITROGEN CONTAINING ULTRATHIN EPITAXIAL STRUCTURES FOR DEVICES	201080045881.9	8/20/10	China	
PLANT AND METHOD FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF GALLIUM NITRIDE BOULES	201110043667.6	2/22/11	China	
IMPROVED SEMI-INSULATING GROUP III METAL NITRIDE AND METHOD OF MANUFACTURE	201110061625.5	3/11/11	China	
REFLECTION MODE PACKAGE FOR OPTICAL DEVICES USING GALLIUM AND NITROGEN CONTAINING MATERIALS	201180008389.9	2/3/11	China	
WHITE LIGHT APPARATUS AND METHOD	201180017677.0	2/3/11	China	
GALLIUM AND NITROGEN CONTAINING TRIANGULAR OR DIAMOND-SHAPED CONFIGURATION FOR OPTICAL DEVICES	201180029188.7	6/20/11	China	
SYSTEM AND METHOD FOR SELECTED PUMP LEDS WITH MULTIPLE PHOSPHORS	201180040221.6	8/19/11	China	

HIGH INTENSITY LIGHT SOURCE	201180054397.7	10/7/11	China	
METHODS AND SYSTEMS FOR EPITAXIAL PROCESSES ON MISCUT BULK SUBSTRATES	201210098117.9	4/5/12	China	
IMPROVED ACCESSORIES FOR LED LAMPS	201210322687.1	9/3/12	China	
HEATSINK FOR LED	201230029505.2	2/15/12	China	
HEATSINK	201230600658.8	12/4/12	China	
DENSE-LUMINESCENT-MATERIALS-COATED VIOLET LEDS	201310718453.3	12/23/13	China	
SEMICONDUCTOR DIE	201330248472.5	6/13/13	China	
ARRAY OF SEMICONDUCTOR DICE	201330292311.6	6/28/13	China	
LED LAMP	201330545417.2	11/14/13	China	
LED LAMP	2014301700168	6/6/14	China	
LED LAMP	2014301701620	6/6/14	China	
LED LAMP	2014301702214	6/6/14	China	
LED LAMP	2014301703448	6/6/14	China	
POWER LIGHT EMITTING DIODE AND METHOD WITH CURRENT DENSITY OPERATION	201080052148.X	9/20/10	China	
LED LAMPS WITH IMPROVED QUALITY OF LIGHT	201310163390.X	5/6/13	China	

Patent Licenses:

Name/Date of License Agreement	Name of Licensor	Expiration Date of License
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	All remain in effect in perpetuity until the last patent expires.
LOW VOLTAGE LASER DIODES ON {20-21} GALLIUM AND NITROGEN CONTAINING SUBSTRATES	Soraa Laser Diode, Inc.	
METHOD FOR MANUFACTURING GALLIUM AND NITROGEN BEARING LASER DEVICES WITH IMPROVED USAGE OF SUBSTRATE MATERIAL	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
LOW VOLTAGE LASER DIODES ON {20-21} GALLIUM AND NITROGEN CONTAINING SUBSTRATES	Soraa Laser Diode, Inc.	
LASER PACKAGE HAVING MULTIPLE EMITTERS CONFIGURED ON A SUBSTRATE MEMBER	Soraa Laser Diode, Inc.	
OPTICAL MODULE APPARATUS	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
GAN-BASED VCSELS WITH POLARIZED EMISSION	Soraa Laser Diode, Inc.	
INTEGRATED TOTAL INTERNAL REFLECTORS FOR HIGH-GAIN LASER DIODES WITH HIGH QUALITY CLEAVED FACETS ON NONPOLAR/SEMIPOLAR GAN SUBSTRATES	Soraa Laser Diode, Inc.	
SELF-ALIGNED MULTI-DIELECTRIC-LAYER LIFT OFF PROCESS FOR LASER DIODE STRIPES	Soraa Laser Diode, Inc.	

SOLID STATE LASER DEVICE USING A SELECTED CRYSTAL ORIENTATION IN NON-POLAR OR SEMI-POLAR GAN CONTAINING MATERIALS AND METHODS	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING MISCUT GAN SUBSTRATES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES AND GROWTH STRUCTURES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES AND GROWTH STRUCTURES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES AND GROWTH STRUCTURES FOR LASER APPLICATIONS OF EMISSIONS OF 500 NM AND GREATER	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING NON-POLAR GAN SUBSTRATES AND GROWTH STRUCTURES FOR LASER APPLICATIONS IN 481 NM	Soraa Laser Diode, Inc.	
GALLIUM NITRIDE BASED LASER DAZZLING DEVICE AND METHOD	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
GROWTH STRUCTURES AND METHOD FOR FORMING LASER DIODES ON {20-21} OR OFF CUT GALLIUM AND NITROGEN CONTAINING SUBSTRATES	Soraa Laser Diode, Inc.	
LOW VOLTAGE LASER DIODES ON {20-21} GALLIUM AND NITROGEN CONTAINING SUBSTRATES	Soraa Laser Diode, Inc.	
GROWTH STRUCTURES AND METHOD FOR FORMING LASER DIODES ON {30-31} OR OFF CUT GALLIUM AND NITROGEN CONTAINING SUBSTRATES	Soraa Laser Diode, Inc.	
METHOD OF FABRICATING OPTICAL DEVICES USING LASER TREATMENT	Soraa Laser Diode, Inc.	
TAPERED HORIZONTAL GROWTH CHAMBER	Soraa Laser Diode, Inc.	
METHOD AND SYSTEM FOR PROVIDING BIDIRECTIONAL LIGHT SOURCES WITH BROAD SPECTRUM	Soraa Laser Diode, Inc.	
SYSTEM AND METHOD OF MULTI-WAVELENGTH LASER APPARATUS	Soraa Laser Diode, Inc.	
METHOD OF STRAIN ENGINEERING AND RELATED OPTICAL DEVICE USING A GALLIUM AND NITROGEN CONTAINING ACTIVE REGION	Soraa Laser Diode, Inc.	
METHOD OF FABRICATING OPTICAL DEVICES USING LASER TREATMENT OF CONTACT REGIONS OF GALLIUM AND NITROGEN CONTAINING MATERIAL	Soraa Laser Diode, Inc.	

OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES AND GROWTH STRUCTURE FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
LASER PACKAGE HAVING MULTIPLE EMITTERS CONFIGURED ON A SUBSTRATE MEMBER	Soraa Laser Diode, Inc.	
METHOD AND STRUCTURE FOR LASER DEVICES USING OPTICAL BLOCKING REGIONS	Soraa Laser Diode, Inc.	
LASER DIODES WITH SCRIBE STRUCTURES	Soraa Laser Diode, Inc.	
SELF-ALIGNED MULTI-DIELECTRIC-LAYER LIFT OFF PROCESS FOR LASER DIODE STRIPES	Soraa Laser Diode, Inc.	
LASER PACKAGE HAVING MULTIPLE EMITTERS WITH COLOR WHEEL	Soraa Laser Diode, Inc.	
INTEGRATED LASER DIODES WITH QUALITY FACETS ON GAN SUBSTRATES	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES AND GROWTH STRUCTURES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
SOLID STATE LASER DEVICE USING A SELECTED CRYSTAL ORIENTATION IN NON-POLAR OR SEMI-POLAR GAN CONTAINING MATERIALS AND METHODS	Soraa Laser Diode, Inc.	
LASER DEVICES USING A SEMIPOLAR PLANE	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
LASER PACKAGE HAVING MULTIPLE EMITTERS CONFIGURED ON A SUPPORT MEMBER	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
GALLIUM NITRIDE BASED LASER DAZZLING DEVICE AND METHOD	Soraa Laser Diode, Inc.	
METHODS AND APPARATUS FOR PHOTONIC INTEGRATION IN NON-POLAR AND SEMI-POLAR ORIENTED WAVE-GUIDED OPTICAL DEVICES	Soraa Laser Diode, Inc.	
METHOD AND STRUCTURE FOR LASER DEVICES USING OPTICAL BLOCKING REGIONS	Soraa Laser Diode, Inc.	
LASER DEVICES HAVING A GALLIUM AND NITROGEN CONTAINING SEMIPOLAR SURFACE ORIENTATION	Soraa Laser Diode, Inc.	
GROUP III-NITRIDE LASER DIODE GROWN ON A SEMI-POLAR ORIENTATION OF GALLIUM AND NITROGEN CONTAINING SUBSTRATES	Soraa Laser Diode, Inc.	

FACET ON A GALLIUM AND NITROGEN CONTAINING LASER DIODE	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
METHOD AND SYSTEM FOR PROVIDING DIRECTIONAL LIGHT SOURCES WITH BROAD SPECTRUM	Soraa Laser Diode, Inc.	
MAGNESIUM BASED GETTERING REGIONS FOR GALLIUM AND NITROGEN CONTAINING LASER DIODE DEVICES	Soraa Laser Diode, Inc.	
NARROW SIZED LASER DIODE	Soraa Laser Diode, Inc.	
HIGH OPERATING TEMPERATURE LASER DIODES	Soraa Laser Diode, Inc.	
GALLIUM NITRIDE BASED LASER DAZZLING DEVICE AND METHOD	Soraa Laser Diode, Inc.	
GALLIUM AND NITROGEN CONTAINING LASER DIODE DAZZLING DEVICES AND METHODS OF USE	Soraa Laser Diode, Inc.	
LASER DIODES WITH AN ETCHED FACET AND SURFACE TREATMENT	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
METHOD AND SYSTEM FOR PROVIDING DIRECTIONAL LIGHT SOURCES WITH BROAD SPECTRUM	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GaN SUBSTRATES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
SEMICONDUCTOR LASER DIODE ON TILED GALLIUM CONTAINING MATERIAL	Soraa Laser Diode, Inc.	
LASER PACKAGE HAVING MULTIPLE EMITTERS CONFIGURED ON A SUBSTRATE MEMBER	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
LOW VOLTAGE LASER DIODES ON {20-21} GALLIUM AND NITROGEN CONTAINING SUBSTRATES	Soraa Laser Diode, Inc.	
SYSTEM AND METHOD OF MULTI-WAVELENGTH LASER APPARATUS	Soraa Laser Diode, Inc.	
GAN-BASED VCSELS WITH POLARIZED EMISSION	Soraa Laser Diode, Inc.	

SELF-ALIGNED MULTI-DIELECTRIC-LAYER LIFT OFF PROCESS FOR LASER DIODE STRIPES	Soraa Laser Diode, Inc.	
INTEGRATED TOTAL INTERNAL REFLECTORS FOR HIGH-GAIN LASER DIODES WITH HIGH QUALITY CLEAVED FACETS ON NONPOLAR/SEMIPOLAR GAN SUBSTRATES	Soraa Laser Diode, Inc.	
SOLID STATE LASER DEVICE USING A SELECTED CRYSTAL ORIENTATION IN NON-POLAR OR SEMI-POLAR GAN CONTAINING MATERIALS AND METHODS	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING MISCUT GAN SUBSTRATES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
GROWTH STRUCTURES ON NONPOLAR/SEMIPOLAR GAN	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES AND GROWTH STRUCTURES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES AND GROWTH STRUCTURES FOR LASER APPLICATIONS OF EMISSIONS OF 500 NM AND GREATER	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES AND GROWTH STRUCTURES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES AND GROWTH STRUCTURES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING NON-POLAR GAN SUBSTRATES AND GROWTH STRUCTURES FOR LASER	Soraa Laser Diode, Inc.	
LASER DAZZLER AND METHOD	Soraa Laser Diode, Inc.	
LASER DISPLAY AND METHOD	Soraa Laser Diode, Inc.	
PICO PROJECTOR METHOD AND APPARATUS	Soraa Laser Diode, Inc.	
GROWTH STRUCTURES AND METHODS FOR FORMING LASER DIODES ON {20-21} OR OFF CUT GALLIUM AND NITROGEN CONTAINING SUBSTRATES	Soraa Laser Diode, Inc.	
LOW VOLTAGE LASER DIODES ON {20-21} GALLIUM AND NITROGEN CONTAINING SUBSTRATES	Soraa Laser Diode, Inc.	
METHOD OF FABRICATING OPTICAL DEVICES USING LASER TREATMENT	Soraa Laser Diode, Inc.	
TAPERED HORIZONTAL GROWTH CHAMBER	Soraa Laser Diode, Inc.	
METHOD AND SYSTEM FOR PROVIDING DIRECTIONAL LIGHT SOURCES WITH BROAD SPECTRUM	Soraa Laser Diode, Inc.	

SYSTEM AND METHOD OF MULTI-WAVELENGTH LASER APPARATUS	Soraa Laser Diode, Inc.	
LASER DIODES WITH SCRIBE STRUCTURES	Soraa Laser Diode, Inc.	
HIGH POWER LASER DEVICES	Soraa Laser Diode, Inc.	
METHOD OF STRAIN ENGINEERING AND RELATED OPTICAL DEVICE USING A GALLIUM AND NITROGEN CONTAINING ACTIVE REGION	Soraa Laser Diode, Inc.	
LASER PACKAGE HAVING MULTIPLE EMITTERS	Soraa Laser Diode, Inc.	
METHOD AND STRUCTURE FOR LASER DEVICES USING OPTICAL BLOCKING REGIONS	Soraa Laser Diode, Inc.	
LASER PACKAGE HAVING MULTIPLE EMITTERS	Soraa Laser Diode, Inc.	
LASER DIODES WITH SCRIBE STRUCTURES	Soraa Laser Diode, Inc.	
METHOD AND STRUCTURE FOR LASER DEVICES USING SELECTED SEMIPOLAR PLANES	Soraa Laser Diode, Inc.	
METHODS AND APPARATUSES FOR PHOTONIC INTEGRATION IN NON-POLAR AND SEMI-POLAR ORIENTED WAVE-GUIDED OPTICAL DEVICES	Soraa Laser Diode, Inc.	
GROUP III-NITRIDE LASER DIODE GROWN ON SEMI-POLAR ORIENTATION OF GALLIUM NITRIDE	Soraa Laser Diode, Inc.	
METHODS FOR MANUFACTURING A FACET ON LASER DIODES	Soraa Laser Diode, Inc.	
GROUP III-NITRIDE LASER DIODES GROWN ON A SEMI-POLAR ORIENTATION OF GALLIUM NITRIDE	Soraa Laser Diode, Inc.	
NARROW SIZED LASER DIODE DEVICE	Soraa Laser Diode, Inc.	
HIGH OPERATING TEMPERATURE LASER DIODES	Soraa Laser Diode, Inc.	
LASER DEVICES HAiVNG A GALLIUM AND NITROGEN CONTAINING SEMIPOLAR SURFACE ORIENTATION	Soraa Laser Diode, Inc.	
LASER DIODES WITH AN ETCHED FACET AND SURFACE TREATMENT	Soraa Laser Diode, Inc.	
GALLIUM NITRIDE CONTAINING LASER DEVICE CONFIGURED ON A PATTERNED SUBSTRATE	Soraa Laser Diode, Inc.	
RED-GREEN-BLUE LASER MODULE	Soraa Laser Diode, Inc.	

GALLIUM AND NITROGEN CONTAINING LASER DEVICE HAVING CONFINEMENT REGION	Soraa Laser Diode, Inc.	
PATTERNED COLOR CONVERTING ELEMENT FOR LASER DIODE	Soraa Laser Diode, Inc.	
TAPERED HORIZONTAL GROWTH CHAMBER	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING GAN SUBSTRATES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
LASER BASED DISPLAY METHOD AND SYSTEM	Soraa Laser Diode, Inc.	
LOW VOLTAGE LASER DIODES ON {20-21} GALLIUM AND NITROGEN CONTAINING SUBSTRATES	Soraa Laser Diode, Inc.	
SYSTEM AND METHOD OF MULTI-WAVELENGTH LASER APPARATUS	Soraa Laser Diode, Inc.	
METHOD OF FABRICATING OPTICAL DEVICES USING LASER TREATMENT OF CONTACT REGIONS OF GALLIUM AND NITROGEN CONTAINING MATERIAL	Soraa Laser Diode, Inc.	
LOW VOLTAGE LASER DIODES ON {20-21} GALLIUM AND NITROGEN CONTAINING SUBSTRATES	Soraa Laser Diode, Inc.	
GROWTH STRUCTURES AND METHODS FOR OPTICAL DEVICES COMPOSED OF GAN MATERIALS	Soraa Laser Diode, Inc.	
MONOLITHICALLY INTEGRATED GREEN AND BLUE LASER DIODES ON NONPOLAR AND SEMIPOLAR GAN	Soraa Laser Diode, Inc.	
SELF ALIGNED RIDGE STRIPE FOR LASER USING PHOTO ELECTRICAL CHEMICAL ETCHING PROCESS	Soraa Laser Diode, Inc.	
SOLID STATE LASER DEVICE USING A SELECTED CRYSTAL ORIENTATION IN NON-POLAR OR SEMI-POLAR GAN CONTAINING MATERIALS AND METHODS	Soraa Laser Diode, Inc.	
OPTICAL DEVICE STRUCTURE USING MISCUT GAN SUBSTRATES FOR LASER APPLICATIONS	Soraa Laser Diode, Inc.	
FACETS IN HIGH-POWER LASERS + PROCESS + MATERIALS IMPROVEMENTS	Soraa Laser Diode, Inc.	
A LASER DIODES WITH AN ETCHED FACET AND SURFACE	Soraa Laser Diode, Inc.	
UTILITY PATENT APPLICATION: OPTICAL MODULE DEVICE EMITTING VISIBLE LIGHT	Soraa Laser Diode, Inc.	
LASER PACKAGE HAVING MULTIPLE BLUE- VIOLET EMITTERS CONFIGURED ON A SUPPORT MEMBER	Soraa Laser Diode, Inc.	
GREEN LASER	Soraa Laser Diode, Inc.	

PATTERNED COLOR CONVERTING ELEMENT FOR LASER DIODE	Soraa Laser Diode, Inc.	
ULTRA-HIGH CONFINEMENT RIDGE LASER CAVITY	Soraa Laser Diode, Inc.	
ULTRA-HIGH CONFINEMENT RIDGE LASER CAVITY	Soraa Laser Diode, Inc.	
GALLIUM AND NITROGEN CONTAINING LASER DEVICE HAVING CONFINEMENT REGION	Soraa Laser Diode, Inc.	

SEE ALSO THE PATENT LICENSES LISTED BELOW UNDER "RESTRICTED LICENSES"

Trademarks and Trademark Applications:

U.S.

Trademark	Serial Number	Registration Number	Date of Filing	Jurisdiction of Filing	Name of trademark holder if other than Borrower
SORAA	86058247		September 6, 2013	United States of America	
SORAA SNAP SYSTEM	85895887		April 4, 2013	United States of America	
SIMPLY PERFECT	85495244		December 14, 2011	United States of America	
SIMPLY PERFECT LIGHT	85870246	4431751	March 7, 2013	United States of America	
SORAA	85594716	4385048	April 11, 2012	United States of America	
SORAA GAN ON GAN	85593900	4336144	April 10, 2012	United States of America	
SORAA	77982688	4150651	October 5, 2009	United States of America	

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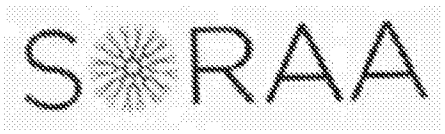
Trademark	Class	Trademark Application Number	Date of Application	Jurisdiction of Filing	Status	Name of application holder if other than Borrower
SORAA	9	9364715	4/20/11	China	Registered	
SORAA	11	9364714	4/20/11	China	Preliminary published on May 13, 2014	
SORAA	42	9364713	5/21/12	China	Registered	

	11	10944301	5/21/12	China	Pending for the first instance of TRAB review of refusal	
SORAA	9;11;42	9829409	3/22/11	European Union	Registered	
SORAA	9;11;42	45-2011-2096	5/18/11	Korea	Registered	
SORAA	9;11;42	2011-033532	5/17/11	Japan	Registered	
SORAA	9;11;42	100027849	6/3/11	Taiwan	Registered.	

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Exclusive License Agreement, dated as of October 1, 2012, by and between Borrower and The Regents of the University of California, a California corporation, acting through its Santa Barbara campus	The Regents of the University of California, a California corporation, acting through its Santa Barbara campus	Continues so long as licensee pays the applicable royalty fees thereunder. The term of the license expires when the last patent licensed thereunder expires.
Non-Exclusive License Agreement, dated as of January 2, 2008, by and between SJS Technology, Inc. and The Regents of the University of California, a California corporation, acting through its Santa Barbara campus	The Regents of the University of California, a California corporation, acting through its Santa Barbara campus	Continues so long as licensee pays the applicable royalty fees thereunder. The term of the license expires when the last patent licensed thereunder expires.
Non-Exclusive License Agreement, dated as of January 18, 2008, by and between KAAI Inc. and The Regents of the University of California, a California corporation, acting through its Santa Barbara campus	The Regents of the University of California, a California corporation, acting through its Santa Barbara campus	Continues so long as licensee pays the applicable royalty fees thereunder. The term of the license expires when the last patent licensed thereunder expires.

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